

Amendments to the Abstract:

Please replace the Abstract with the following:

A method of filling a gap ~~which is defined by adjacent raised features on a~~ substrate includes providing flows a flow of a silicon-containing processing gas to a chamber ~~housing the substrate, providing a flow of an oxidizing processing gas to the chamber, and~~ providing a flow of a phosphorous-containing processing gas to the a chamber housing the ~~substrate and . The method also includes depositing a first portion of a P-doped silicon oxide~~ film as a substantially conformal layer in the gap by causing a reaction ~~between the silicon-~~ containing processing gas, the phosphorous-containing processing gas, and the oxidizing among ~~the processing gases and . Depositing the conformal layer includes varying over time a ratio of~~ the ~~(silicon-containing processing gas plus phosphorous-containing processing gas):(oxidizing~~ processing gas) gases. The temperature and maintaining the temperature of the substrate is ~~maintained~~ below about 500°C throughout deposition of the conformal layer. The method also includes depositing a second portion of the P-doped silicon oxide film as a bulk layer. ~~Depositing a second portion of the film includes by maintaining the ratio of the (silicon-~~ containing processing gas plus phosphorous-containing processing gas):(oxidizing processing ~~gas) gases substantially constant throughout deposition of the bulk layer. The and maintaining~~ the temperature of the substrate is maintained below about 500°C throughout deposition of the bulk layer.